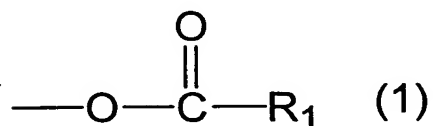


CLAIMS

1. An underlayer coating forming composition comprising a dextrin ester compound that at least 50% of hydroxy groups in dextrin is converted into ester groups of formula (1):



wherein R₁ is C₁₋₁₀alkyl group that may be substituted with hydroxy group, carboxyl group, cyano group, nitro group, C₁₋₆alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C₁₋₆alkoxycarbonyl group, or a phenyl group, a naphthyl group or an anthryl group that may be substituted with C₁₋₆alkyl group, hydroxy group, carboxyl group, cyano group, nitro group, C₁₋₆alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C₁₋₆alkoxycarbonyl group, a crosslinking compound, and an organic solvent.

2. An underlayer coating forming composition comprising a dextrin ester compound that at least 50% of hydroxy groups in dextrin is converted into ester groups of formula (1) wherein R₁ has the same meaning as that defined in claim 1, and that has a weight average molecular weight of 4000 to 20000, a crosslinking compound, and an organic solvent.
3. The underlayer coating forming composition according to claim 1 or 2, further comprising an acid compound or an acid generator.
4. A method for forming photoresist pattern for use in manufacture of semiconductor device, comprising the steps of:
coating the underlayer coating forming composition according to any one of claims 1 to 3 on a semiconductor substrate, and baking it to form an underlayer coating;
forming a photoresist layer on the underlayer coating;
exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and
developing the photoresist layer after the exposure to light.
5. The underlayer coating forming composition according to claim 1 or 2, in which

the composition is used for forming an underlayer coating by coating the composition on a semiconductor substrate having a hole with an aspect ratio shown in height/diameter of 1 or more, and baking it.